

TSMC-02-246



March 9, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/762,164 01/21/04 |  
Liang-Gi Yao et al.  
NOBLE HIGH-K DEVICE  
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#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on March 16, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 3/16/04

U.S. Patent 6,310,367 to Yagishita et al., "MOS Transistor Having a Tensile-Strained Si Layer and a Compressive-Strained Si-Ge Layer," describes a strained Si and high-k gate dielectric Tx process.

U.S. Patent 5,357,119 to Wang et al., "Field Effect Devices Having Short Period Superlattice Structures Using Si and Ge," describes an SiGe and gate oxide process.

U.S. Patent 6,353,249 to Boyd et al., "MOSFET with High Dielectric Constant Gate Insulator and Minimum Overlap Capacitance," describes an SiGe substrate and high-k gate dielectric.

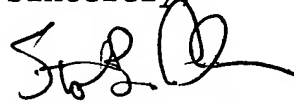
U.S. Patent 6,271,094 to Boyd et al., "Method of Making MOSFET with High Dielectric Constant Gate Insulator and Minimum Overlap Capacitance," discloses methods of fabricating metal oxide semiconductor field effect transistor (MOSFET) devices.

U.S. Patent 6,335,238 to Hanttangady et al., "Integrated Dielectric and Method," discusses reaction barriers between high-k dielectrics and an underlying Group IV semiconductor layer.

TSMC-02-246

U.S. Patent 6,287,903 to Okuno et al., "Structure and Method for a Large-Permittivity Dielectric Using a Germanium Layer," describes a structure and method for a large-permittivity dielectric using a germanium layer.

Sincerely,

A handwritten signature in black ink, appearing to read "S. B. Ackerman", with a large, stylized flourish at the end.

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

TSMC-02-246

Application Number

10/762,164

Applicant

Liang-Gi Yao et al.

Filing Date

01/21/04

Group Art Unit

## U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE & APPROPRIATE
QIPE	6310367	10/30/01	Yagishita et al.	257	190	2/22/00
MAR 19 2004	5357119	10/18/94	Wang et al.	257	18	2/19/93
	6353249	3/5/02	Boyd et al.	257	369	5/25/01
	6271094	8/7/01	Boyd et al.	438	287	2/14/00
	6335238	1/1/02	Hanttangady et al.	438	240	5/5/98
	6287903	9/11/01	Okuno et al.	438	197	12/21/98

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Portinorx Pages, Etc.)


EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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ASSOCIATE POWER OF ATTORNEY

I hereby appoint Stephen G. Stanton, registration number 35,690, as my associate attorney in this case. His telephone number is (610) 296-5194.

Please continue to direct all correspondence in this case to the undersigned attorney.

Respectfully submitted,

Stephen B. Ackerman,

Principal attorney of record